

Description

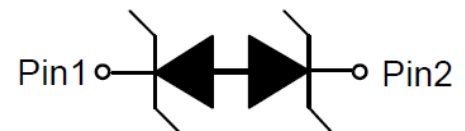
The XE2FUC5VB is an ultra-low capacitance ESD protection diode designed to protect sensitive electronic components which are connected to high speed data lines and control lines from over-stress caused by ESD (Electrostatic Discharge), EFT (Electrical Fast Transients) and Lightning. The XE2FUC5VB may be used to provide ESD protection up to $\pm 20\text{kV}$ (contact) and $\pm 20\text{kV}$ (air) discharge according to IEC61000-4-2, and withstand peak pulse current up to 5A (8/20 μs) according to IEC61000-4-5.

The XE2FUC5VB is available in DFN1006-2L package. Standard products are Pb-free and Halogen-free.

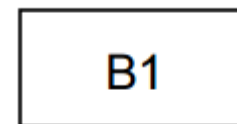
<http://www.xihangsemi.com>



DFN1006-2L (Bottom View)



Circuit Diagram



Marking (Top View)

Features

- ◆ Working voltage: 5V
- ◆ DFN1006-2L Package
- ◆ Ultra Low Capacitance: 0.35pF
- ◆ Transient protection for data lines to IEC61000-4-2 (ESD) $\pm 20\text{kV}$ (air), $\pm 20\text{kV}$ (contact)
- ◆ IEC61000-4-5 (Surge) 5A (8/20 μs)
- ◆ IEC61000-4-4(EFT)40A(5/50ns)
- ◆ Low leakage current
- ◆ Low clamping voltage
- ◆ Solid-state silicon-avalanche technology

Applications

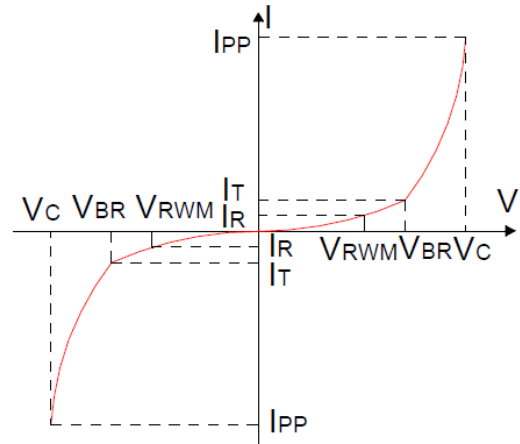
- ◆ USB2.0 and USB3.0
- ◆ HDMI1.3 and HDMI1.4
- ◆ SATA and eSATA
- ◆ DVI
- ◆ IEEE1394
- ◆ PCI Express
- ◆ Portable Electronics
- ◆ Notebook

Order Information

Device	Package	Shipping
XE2FUC5VB	DFN1006-2L	10000/Tape&Reel

Definitions of electrical characteristics

Symbol	Parameter
V_{RWM}	Reverse Stand-off Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Reverse Breakdown Voltage @ I_T
I_{BR}	Reverse Breakdown Current
I_{PP}	Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
I_T	Test current



Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power ($t_P = 8/20\mu S$)	P_{PK}	100	W
Peak Pulse Current ($t_P = 8/20\mu S$)	I_{pp}	5	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	± 20	kV
ESD according to IEC61000-4-2 contact discharge		± 20	kV
Lead Soldering Temperature	T_L	260 (10 sec)	$^{\circ}C$
Operating Temperature	T_{OP}	-55 to +125	$^{\circ}C$
Storage Temperature	T_{STG}	-55 to +150	$^{\circ}C$

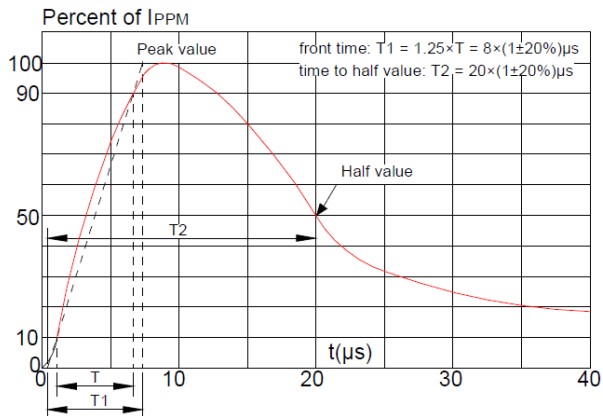
Electrical Characteristics ($T_a=25^{\circ}C$, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Reverse Stand-off Voltage	V_{RWM}				5.0	V
Reverse Leakage Current	I_R	$V_{RWM}=5V$			100	nA
Reverse Breakdown Voltage	V_{BR}	$I_T=1mA$	7.0	8.4	9.0	V
Clamping Voltage ¹⁾	V_C	$I_{PP}=1A \quad t_P = 8/20\mu s$		10	12.5	V
		$I_{PP}=2.5A \quad t_P = 8/20\mu s$		13	15	V
		$I_{PP}=5A \quad t_P = 8/20\mu s$		24	26	V
Junction Capacitance	C_j	$V_R=0V \quad f = 1MHz$		0.35	0.5	pF

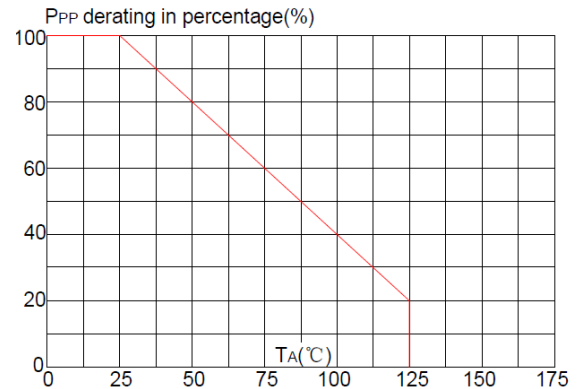
Notes:

1)Non-repetitive current pulse, according to IEC61000-4-5.

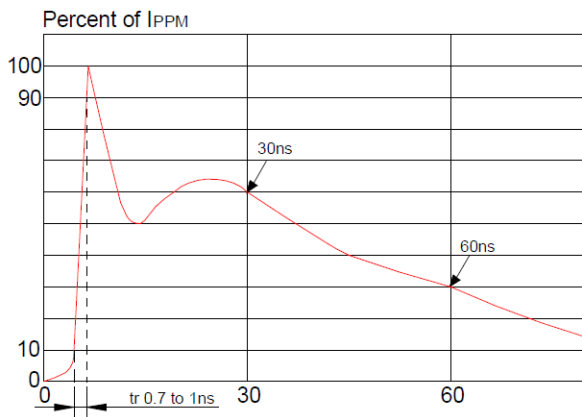
Typical Characteristics (Ta=25°C, unless otherwise noted)



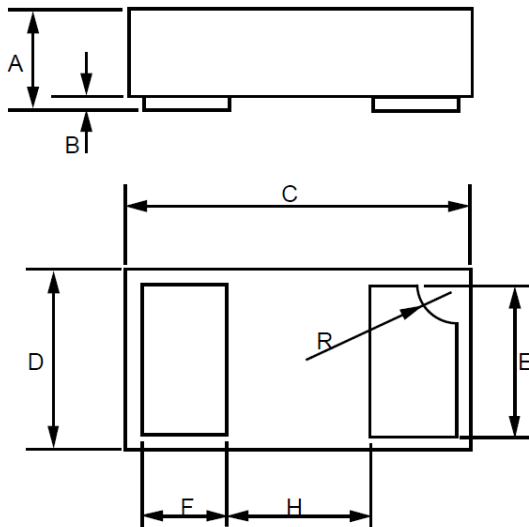
Pulse Waveform (8/20us)



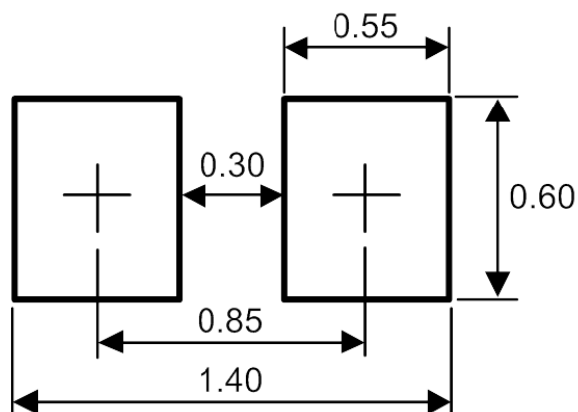
Pulse Derating Curve



ESD Clamping(8kV Contact Discharge)

Package Outline Dimensions (DFN1006-2L)


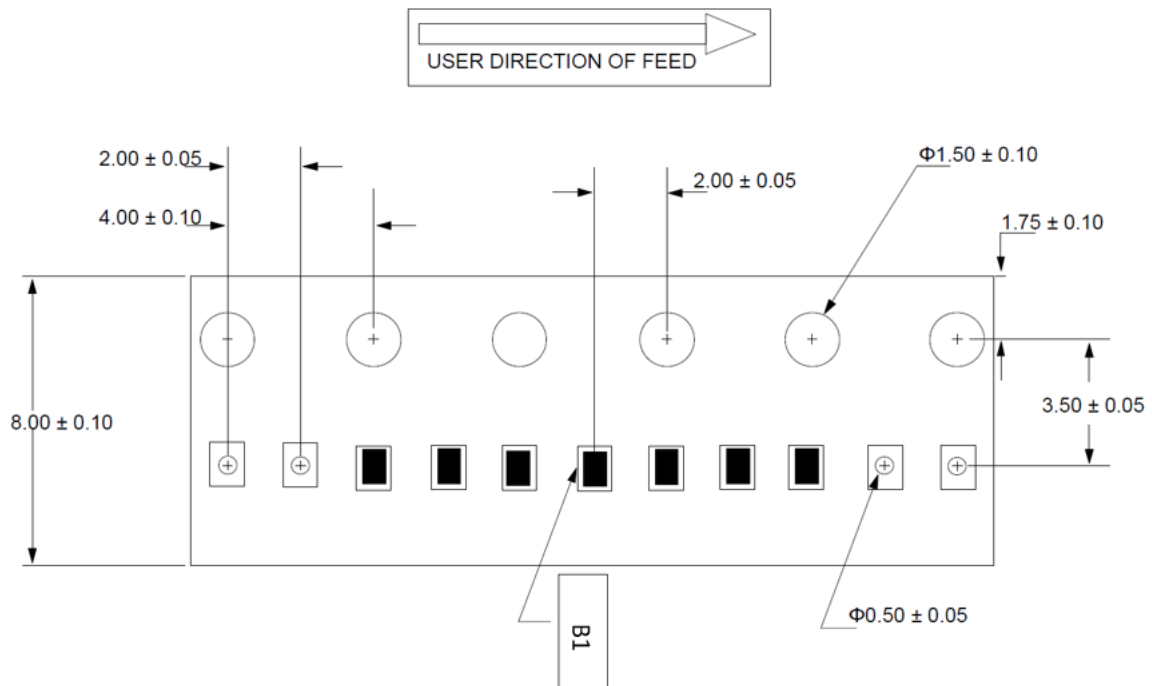
Dim	Inches		Millimeters	
	MIN	MAX	MIN	MAX
A	0.018	0.020	0.46	0.51
B	0.000	0.002	0	0.05
C	0.037	0.041	0.95	1.05
D	0.022	0.025	0.55	0.65
E	0.017	0.021	0.45	0.55
F	0.008	0.012	0.20	0.30
H	0.015Typ.		0.40Typ	
R	0.001	0.005	0.05	0.15

Recommend Land Pattern (Unit: mm)


Note:

This recommended land pattern is for reference purpose only.

Load with information



Unit: mm

NOTICE

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